FUJITSU

256K CMOS ELECTRICALLY ERASABLE PROM

MBM28C256

April 1988
Edition 1.0

256K BIT(32,768 x 8) CMOS ELECTRICALLY ERASABLE PROGRAMMABLE READ ONLY MEMORY

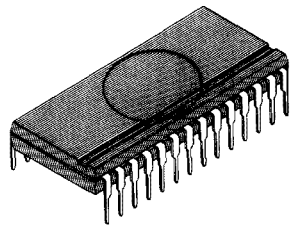
The Fujitsu MBM28C256 is a high speed read-only static memory that is electrically erasable and reprogrammable. The device contains 262,144 reprogrammable bits organized in a 32,768-byte/8-bit format.

The MBM28C256 has a high-voltage generator on chip; which allow to program or erase data using single +5V supply, the write operation can be similar to that of a static RAM.

The MBM28C256 is fabricated using CMOS double polysilicon gate technology with stacked gate cells and housed in a standard 28-pin plastic DIP package.

- 32,768-byte/8-bit organization with on-chip decoding
- Internally latched address/data in writing
- Automatic Erase before Write
- Single-byte or 64-byte programming capability
- Data protection from short write pulse or noise on $\overline{WE}$
- Software data protection
- Chip Erase capability using external power supply
- Write status identificator DATA POLLING
- Single +5V(±10%) power supply with low current drain:
  Active operation : 50 mA max.
  Standby operation: 0.1 mA max.
- Fast access time :
  150 ns max. (MBM28C256-15)
- TTL-compatible inputs/outputs
- Three-state output for wired-OR capability
- Output enable($\overline{OE}$) for simple memory expansion
- Minimum Endurance of 10000 Erase/Write cycle per Byte
- JEDEC approval pin assignment and package
- Standard 28-pin PLASTIC DIP package (600mil): Suffix -P

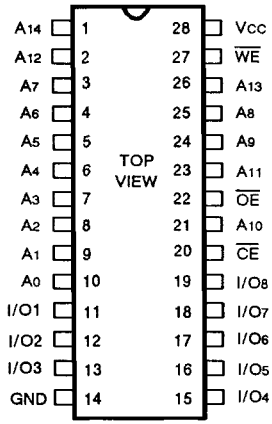
ADVANCE INFORMATION



PLASTIC PACKAGE
(DIP-28P-M02)

6

PIN ASSIGNMENT



This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

6